

IN THE ABSTRACT

Please amend the Abstract as follows:

Abstract of the Disclosure

A method of forming an encapsulating spacer prior to gate stack reoxidation is provided which prevents the formation of undesirable metal oxides during reoxidation. A material such as a thin silicon nitride or amorphous silicon is selectively deposited by limiting deposition time to a period less than incubation time. As a result spacers are formed without having to perform an additional etch act. A selective spacer to prevent metal oxide formation during polycide reoxidation of a feature such as an electrode and a method for forming the selective spacer are disclosed. A material such as a thin silicon nitride or an amorphous silicon film is selectively deposited on the electrode by limiting deposition time to a period less than an incubation time for the material on silicon dioxide near the electrode. The spacer is deposited only on the electrode and not on surrounding silicon dioxide. The spacer serves as a barrier for the electrode during subsequent oxidation to prevent metal oxide formation while allowing oxidation to take place over the silicon dioxide.